

### SANYO Semiconductors DATA SHEET

# ATP404 — General-Purpose Switching Device Applications

#### Features

- Low ON-resistance.
- · Avalanche resistance guarantee.
- Halogen free compliance.

#### Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		60	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		95	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	380	А
Allowable Power Dissipation	PD	Tc=25°C	70	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		214	mJ
Avalanche Current *2	IAV		48	А

Note :\*1 VDD=30V, L=100µH, IAV=48A

\*2 L≤100µH, Single pulse

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	60			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			10	μΑ
Gate-to-Source Leakage Current	IGSS	$V_{GS}=\pm 16V$ , $V_{DS}=0V$			±10	μΑ

Marking : ATP404

Continued on next page.

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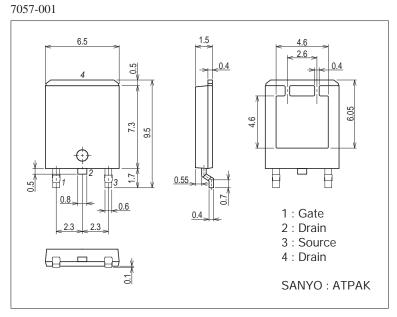
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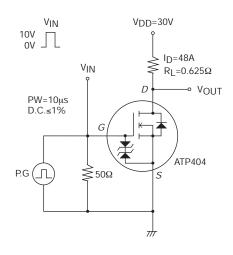
Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =48A		100		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=48A, VGS=10V		5.5	7.2	mΩ
	R <sub>DS</sub> (on)2	ID=48A, VGS=4.5V		7.5	10.5	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		6400		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		490		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =20V, f=1MHz		380		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		53		ns
Rise Time	tr	See specified Test Circuit.		640		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		380		ns
Fall Time	tf	See specified Test Circuit.		520		ns
Total Gate Charge	Qg	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =95A		120		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =95A		25		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =95A		25		nC
Diode Forward Voltage	VSD	IS=95A, VGS=0V		0.95	1.2	V

#### Package Dimensions

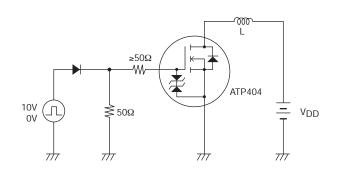
unit : mm (typ)



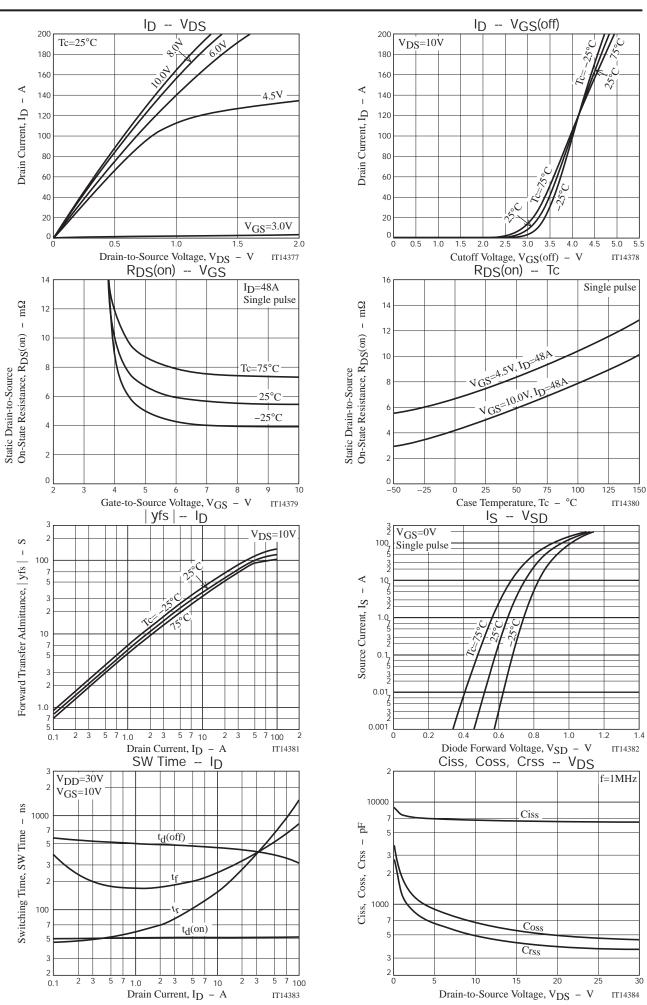
#### Switching Time Test Circuit

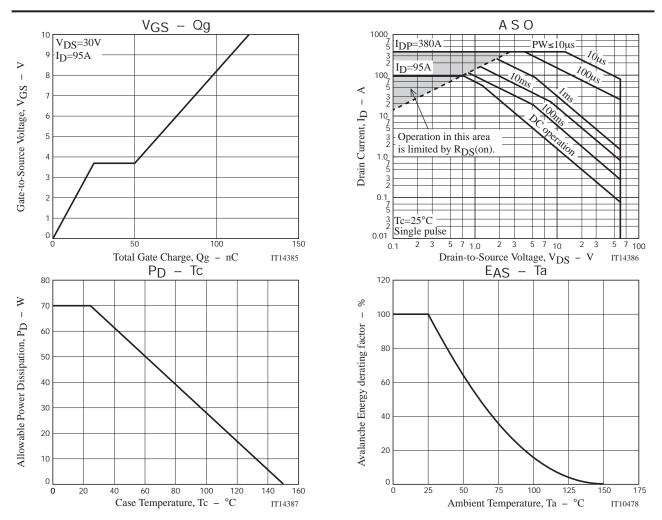


#### Avalanche Resistance Test Circuit



ATP404





## Note on usage : Since the ATP404 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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